

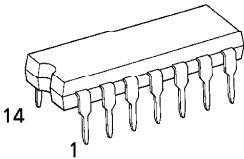
TC74HC4072AP, TC74HC4072AF

DUAL 4-INPUT OR GATE

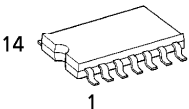
The TC74HC4072A is a high speed CMOS 4-INPUT OR GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 4 stages including buffered outputs, which provide high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

- High Speed..... $t_{pd} = 9\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 1\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC} (\text{Min.})$
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4\text{mA}(\text{Min.})$
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range.... $V_{CC} (\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 4072B

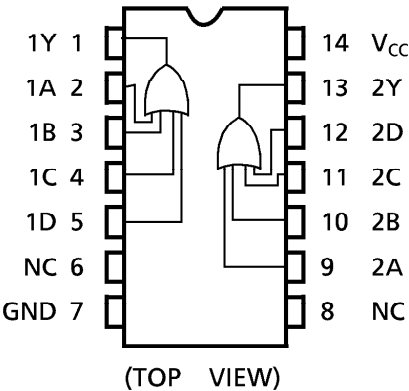


P (DIP14-P-300-2.54)
Weight : 0.96g (Typ.)

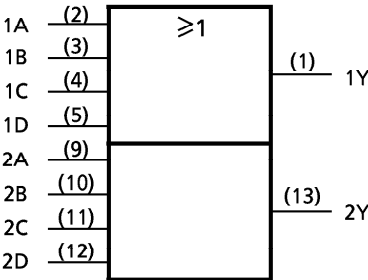


F (SOP14-P-300-1.27)
Weight : 0.18g (Typ.)

PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE

A	B	C	D	Y
H	X	X	X	H
X	H	X	X	H
X	X	H	X	H
X	X	X	H	H
L	L	L	L	L

X : Don't Care

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	$^{\circ}\text{C}$

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$2 \sim 6$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	$^{\circ}\text{C}$
Input Rise and Fall Time	t_r, t_f	$0 \sim 1000$ ($V_{CC} = 2.0\text{V}$) $0 \sim 500$ ($V_{CC} = 4.5\text{V}$) $0 \sim 400$ ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 4.5 6.0	1.50 3.15 4.20	— — —	— — —	1.50 3.15 4.20	— — —	V
Low - Level Input Voltage	V_{IL}		2.0 4.5 6.0	— — —	— — —	0.50 1.35 1.80	— — —	0.50 1.35 1.80	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -20\mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	V
			$I_{OH} = -4 \text{ mA}$ $I_{OH} = -5.2 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	— —	4.13 5.63	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0 4.5 6.0	— — —	0.0 0.0 0.0	— — —	0.1 0.1 0.1	V
			$I_{OL} = 4 \text{ mA}$ $I_{OL} = 5.2 \text{ mA}$	4.5 6.0	— —	0.17 0.18	0.26 0.26	— —	0.33 0.33
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC} \text{ or GND}$	6.0	—	—	± 0.1	—	± 1.0	μA
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC} \text{ or GND}$	6.0	—	—	1.0	—	10.0	

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	4	8	ns
Propagation Delay Time	t_{PLH} t_{PHL}		—	9	16	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.		MAX.
Output Transition Time	t _{TLH} t _{THL}		2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time	t _{pLH} t _{pHL}		2.0	—	36	100	—	125	ns
			4.5	—	12	20	—	25	
			6.0	—	10	17	—	21	
Input Capacitance	C _{IN}		—	5	10	—	10	pF	
Power Dissipation Capacitance	C _{PD} (1)		—	22	—	—	—		

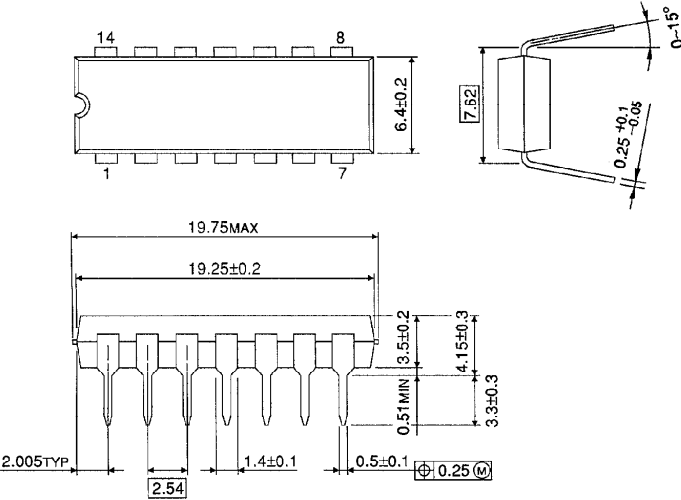
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2 \text{ (per Gate)}$$

DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

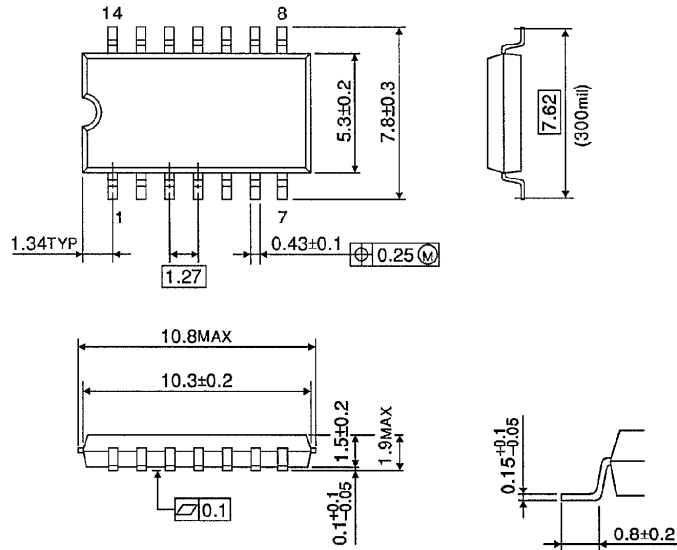
Unit in mm



Weight : 0.96g (Typ.)

SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm



Weight : 0.18g (Typ.)